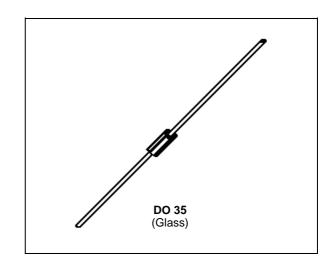
SMALL SIGNAL SCHOTTKY DIODES



DESCRIPTION

General purpose, metal to silicon diodes featuring very low turn-on voltage and fast switching.

These devices have integrated protection against excessive voltage such as electrostatic discharges.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	BAT47	BAT48	Unit	
V_{RRM}	Repetitive Peak Reverse Voltage		20	40	V
I _F	Forward Continuous Current*	T _a = 25 °C	35	mA	
I _{FRM}	Repetitive Peak Fordware Current*	1	А		
I _{FSM}	Surge non Repetitive Forward Current*	t _p = 10ms	7.5		Α
		$t_p = 1s$	1.	.5	
P _{tot}	Power Dissipation*	33	30	mW	
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to - 65 to	°C °C		
TL	Maximum Temperature for Soldering during 10s at 4mm from Case 230				

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-l)}	Junction-ambient*	300	°C/W

^{*} On infinite heatsink with 4mm lead length

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions				Тур.	Max.	Unit
V_{BR}	$I_R = 10\mu A$		BAT47	20			V
	I _R = 25μA		BAT48	40			
V _F *	$T_j = 25^{\circ}C$ $I_F = 0.1 mA$		All Types			0.25	V
	$T_j = 25^{\circ}C$ $I_F = 1mA$					0.3	
	$T_j = 25^{\circ}C$ $I_F = 10mA$					0.4	
	$T_j = 25^{\circ}C$ $I_F = 30mA$		BAT47			0.5	
	$T_j = 25^{\circ}C$ $I_F = 150mA$					0.8	
	$T_j = 25^{\circ}C$ $I_F = 300mA$					1	
	$T_j = 25^{\circ}C$ $I_F = 50mA$		BAT48			0.5	
	$T_j = 25^{\circ}C$ $I_F = 200mA$					0.75	
	$T_j = 25^{\circ}C$ $I_F = 500mA$					0.9	
I _R *	$T_j = 25^{\circ}C$	V _R = 1.5V	All Types			1	μΑ
	$T_j = 60^{\circ}C$					10	
	$T_j = 25^{\circ}C$	V _R = 10V	BAT47			4	
	$T_j = 60^{\circ}C$					20	
	$T_j = 25^{\circ}C$	V _R = 20V				10	
	$T_j = 60^{\circ}C$					30	
	$T_j = 25^{\circ}C$	V _R = 10V	BAT48			2	
	$T_j = 60^{\circ}C$					15	
	$T_j = 25^{\circ}C$	V _R = 20V				5	
	$T_j = 60^{\circ}C$					25	
	T _j = 25°C	V _R = 40V				25	
	$T_j = 60^{\circ}C$					50	

DYNAMIC CHARACTERISTICS

Symbol		Min.	Тур.	Max.	Unit		
С	$T_j = 25^{\circ}C$ $V_R = 0V$	f = 1MHz			20		рF
	$T_j = 25^{\circ}C$ $V_R = 1V$				12		
t _{rr}	$T_j = 25^{\circ}C$ $I_F = 10mA$	$V_R = 1V$ $i_{rr} = 1mA$	$R_L = 100\Omega$		10		ns

^{*} Pulse test: $t_p\!\leq\!300\mu s$ $\delta\!<\!2\%$.



Figure 1. Forward current versus forward voltage at different temperatures (typical values).

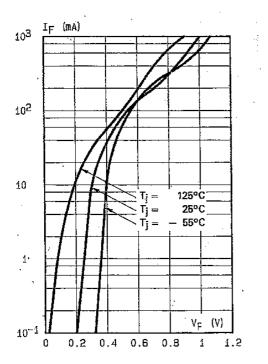


Figure 3. Reverse current versus junction temperature.

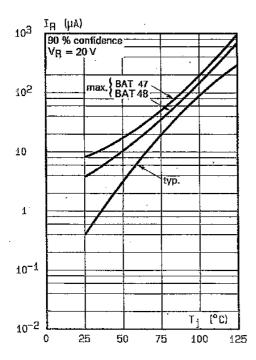


Figure 2. Forward current versus forward voltage (typical values).

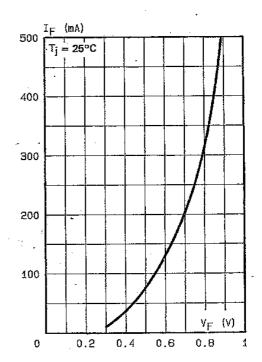


Figure 4. Reverse current versus continuous reverse voltage (typical values).

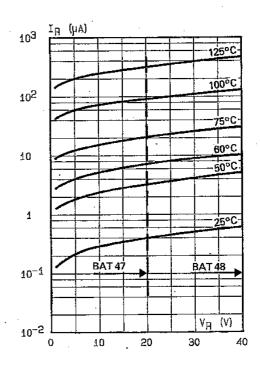
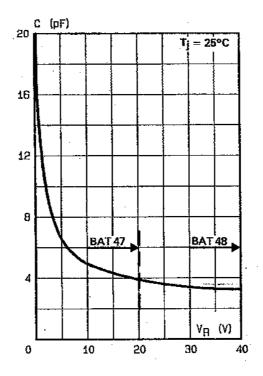
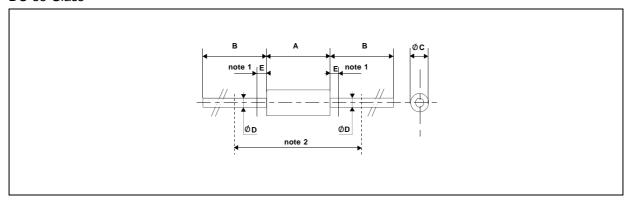


Figure 5. Capacitance C versus reverse applied voltage $V_{\mbox{\scriptsize R}}$ (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



		DIMEN	ISIONS				
REF.	Millimeters		Millimeters Inches		NOTES		
	Min.	Max.	Min.	Max.			
Α	3.050	4.500	0.120	0.117	1 - The lead diameter Ø D is not controlled over zone E		
В	12.7		0.500		2 - The minimum axial lengh within which the device may be		
ØC	1.530	2.000	0.060	0.079	placed with its leads bent at right angles is 0.59"(15 mm)		
Ø D	0.458	0.558	0.018	0.022			
Е		1.27		0.050			

Cooling method: by convection and conduction. Marking: clear, ring at cathode end. Weight: 0.015g

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